

Features

- Trench Power LV MOSFET Technology
- · High Speed Switching
- · Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

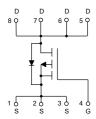
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 54°C/W Junction to Ambient(Note2)
- Thermal Resistance: 2.1°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	-40	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		-35	А	
	T _C =100°C	l _D	-22		
Pulsed Drain Current ^(Note3)		I _{DM}	140	Α	
Total Power Dissipation ^(Note4)		P _D	59	W	
Single Pulsed Avalanche Energy ^(Note5)		E _{AS}	98	mJ	

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. T_J =25°C, V_{DD} =-35V, V_{GS} =10V, L=1mH.

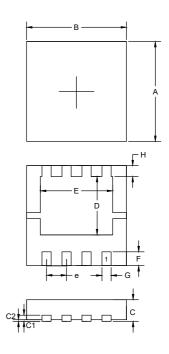
Internal Structure and Marking Code





P-CHANNEL MOSFET

DFN3333



	DIMENSIONS					
DIM IN		HES	MM		NOTE	
וווט	MIN	MAX	MIN	MAX	NOTE	
Α	0.126	0.130	3.20	3.30		
В	0.126	0.130	3.20	3.30		
С	0.030	0.033	0.75	0.85		
C1	0.007	0.009	0.18	0.22		
C2		0.002		0.05		
D	0.071	0.079	1.80	2.00		
Е	0.087	0.098	2.20	2.50		
F	0.016	0.020	0.40	0.50		
G	0.010	0.014	0.25	0.35		
Н	0.012	0.016	0.30	0.40		
е	0.024	0.028	0.60	0.70		



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			·	•			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-40			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V			-1	μΑ	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1	-1.6	-2.5	V	
Drain Cauras On Besistanes	_	V _{GS} =-10V, I _D =-15A	16 20		- 0		
Drain-Source On-Resistance	$R_{DS(on)}$	V _{GS} =-4.5V, I _D =-10A		20	25	mΩ	
Gate Resistance	R _g	f=1MHz, Open Drain		9.5		Ω	
Diode Characteristics							
Continuous Body Diode Current	Is				-35	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.2	V	
Reverse Recovery Time	t _{rr}	1 474 11 / 1/4 4004 /		21.5		ns	
Reverse Recovery Charge	Q _{rr}	I _F =-17A, dI _F /dt=100A/µs		8		nC	
Dynamic Characteristics	1		,		1	1	
Input Capacitance	C _{iss}			2511			
Output Capacitance	C _{oss}	V _{DS} =-25V,V _{GS} =0V,f=1MHz		174		pF	
Reverse Transfer Capacitance	C _{rss}			158			
Total Gate Charge	Qg			57			
Gate-Source Charge	Q_{gs}	V _{DS} =-20V,V _{GS} =-10V,I _D =-3A		9.5		nC	
Gate-Drain Charge	Q_{gd}			9.8			
Turn-On Delay Time	t _{d(on)}			7.3			
Turn-On Rise Time	t _r	V _{DD} =-20V, V _{GS} =-10V,		22.6			
Turn-Off Delay Time	t _{d(off)}	$R_G=6\Omega$, $I_{DS}=-3A$		160		ns	
Turn-Off Fall Time	t _f			53			



Curve Characteristics

0

0

-2

Fig. 1 - Typical Output Characteristics

-100

-80

V_{GS}=-10V,-5V,-4.5V,-4V,-3V,-2.5V

-40

-20

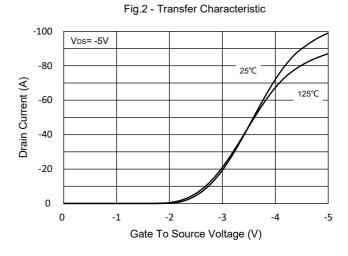
-4

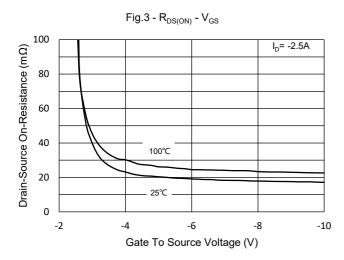
Drain To Source Voltage (V)

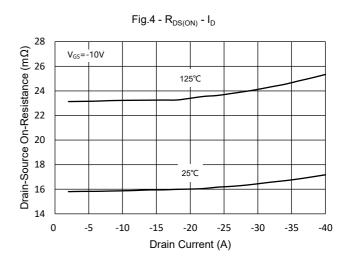
-6

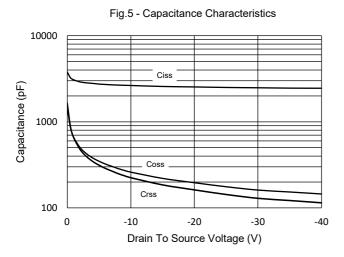
-8

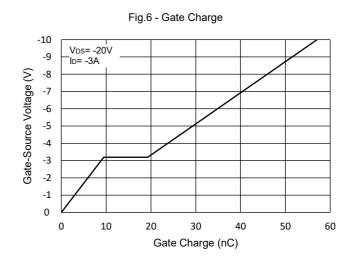
-10







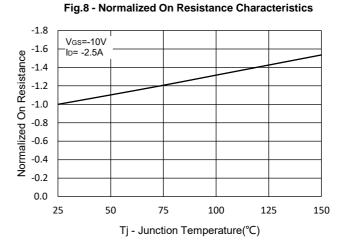


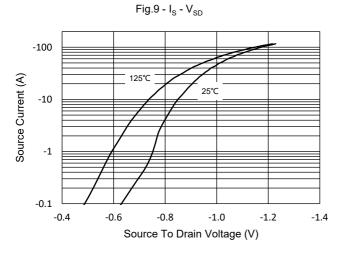


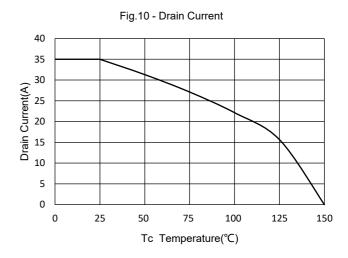


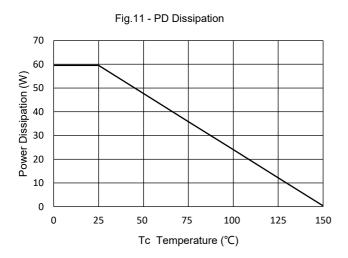
Curve Characteristics

Fig.7 - Normalized Threshold Voltage VGS(th) - Threshold Voltage Normalized -1.2 -1.0 -0.8 ID=-250µA -0.6 -0.4 -0.0 25 50 75 100 125 150 Tj - Junction Temperature(°C)







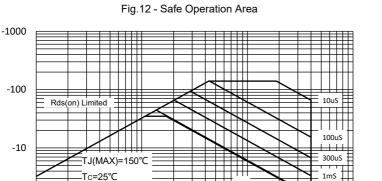




Drain Current (A)

-1 -0.1

Curve Characteristics



Drain-Source Voltage (V)

Single Pulse

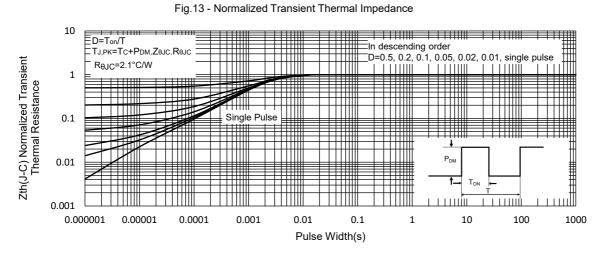
1 1 1 1 1 1 1 1

-10

1mS

10mS

-100





Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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